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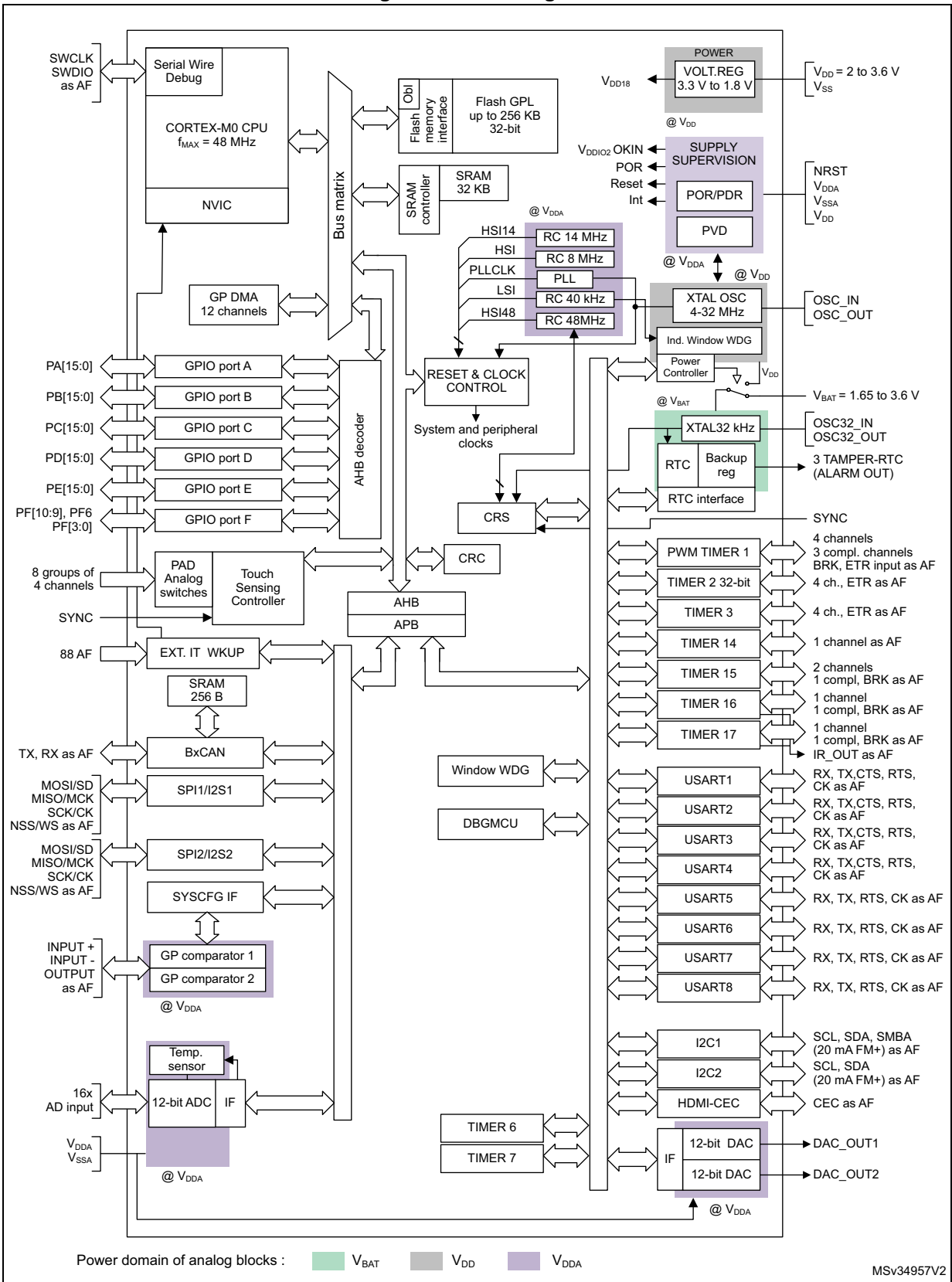
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	88
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f091vct6u

Figure 1. Block diagram



3.19 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI_CEC controller to wakeup the MCU from Stop mode on data reception.

3.20 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.21 Clock recovery system (CRS)

The STM32F091xB/xC embeds a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

3.22 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Figure 4. LQFP100 package pinout

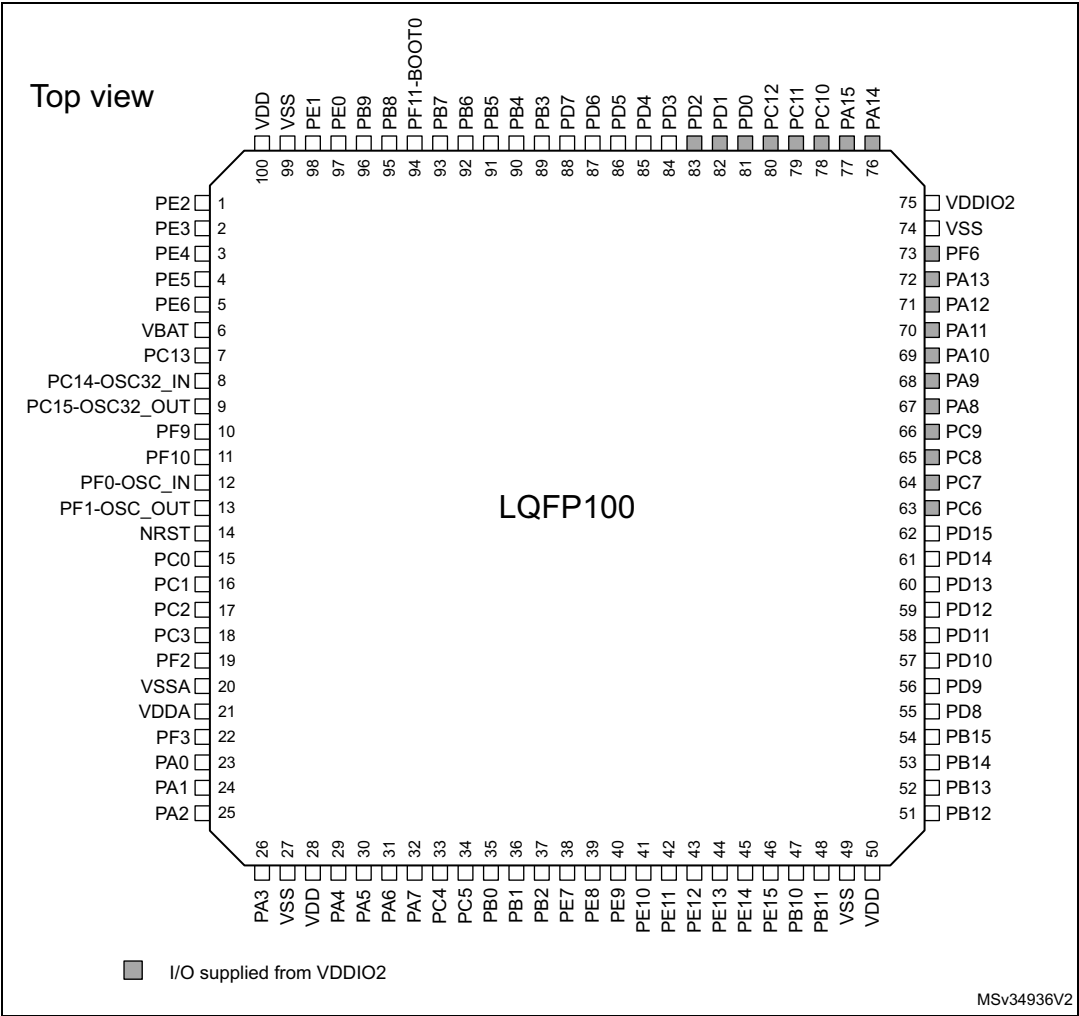


Table 13. STM32F091xB/xC pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UQFPN48					Alternate functions	Additional functions
J1	19	-	-	-	-	PF2	I/O	FT		EVENTOUT, USART7_TX, USART7_CK_RTS	WKUP8
K1	20	F1	12	G8	8	VSSA	S	-		Analog ground	
M1	21	H1	13	H8	9	VDDA	S	-		Analog power supply	
L1	22	-	-	-	-	PF3	I/O	FT		EVENTOUT, USART7_RX, USART6_CK_RTS	
L2	23	G2	14	F7	10	PA0	I/O	TTa		USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1, USART4_TX COMP1_OUT	RTC_TAMP2, WKUP1, ADC_IN0, COMP1_INM6
M2	24	H2	15	F6	11	PA1	I/O	TTa		USART2_RTS, TIM2_CH2, TIM15_CH1N, TSC_G1_IO2, USART4_RX, EVENTOUT	ADC_IN1, COMP1_INP
K3	25	F3	16	E5	12	PA2	I/O	TTa		USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3 COMP2_OUT	ADC_IN2, WKUP4, COMP2_INM6
L3	26	G3	17	H7	13	PA3	I/O	TTa		USART2_RX, TIM2_CH4, TIM15_CH2, TSC_G1_IO4	ADC_IN3, COMP2_INP
D3	27	C2	18	G7	-	VSS	S	-		Ground	
H3	28	D2	19	G6	-	VDD	S	-		Digital power supply	
M3	29	H3	20	H6	14	PA4	I/O	TTa		SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK, USART6_TX	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT1
K4	30	F4	21	F5	15	PA5	I/O	TTa		SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2, USART6_RX	COMP1_INM5, COMP2_INM5, ADC_IN5, DAC_OUT2

Table 13. STM32F091xB/xC pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UQFPN48					Alternate functions	Additional functions
L4	31	G4	22	G5	16	PA6	I/O	TTa		SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT, USART3_CTS	ADC_IN6
M4	32	H4	23	E4	17	PA7	I/O	TTa		SPI1_MOSI, I2S1_SD, TIM3_CH2, TIM14_CH1, TIM1_CH1N, TIM17_CH1, COMP2_OUT, TSC_G2_IO4, EVENTOUT	ADC_IN7
K5	33	H5	24	H5	-	PC4	I/O	TTa		EVENTOUT, USART3_TX	ADC_IN14
L5	34	H6	25	F4	-	PC5	I/O	TTa		TSC_G3_IO1, USART3_RX	ADC_IN15, WKUP5
M5	35	F5	26	G4	18	PB0	I/O	TTa		TIM3_CH3, TIM1_CH2N, TSC_G3_IO2, EVENTOUT, USART3_CK	ADC_IN8
M6	36	G5	27	F3	19	PB1	I/O	TTa		TIM3_CH4, USART3_RTS, TIM14_CH1, TIM1_CH3N, TSC_G3_IO3	ADC_IN9
L6	37	G6	28	H4	20	PB2	I/O	FT		TSC_G3_IO4	-
M7	38	-	-	-	-	PE7	I/O	FT		TIM1_ETR, USART5_CK_RTS	-
L7	39	-	-	-	-	PE8	I/O	FT		TIM1_CH1N, USART4_TX	-
M8	40	-	-	-	-	PE9	I/O	FT		TIM1_CH1, USART4_RX	-
L8	41	-	-	-	-	PE10	I/O	FT		TIM1_CH2N, USART5_TX	-
M9	42	-	-	-	-	PE11	I/O	FT		TIM1_CH2, USART5_RX	-
L9	43	-	-	-	-	PE12	I/O	FT		SPI1_NSS, I2S1_WS, TIM1_CH3N	-
M10	44	-	-	-	-	PE13	I/O	FT		SPI1_SCK, I2S1_CK, TIM1_CH3	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = V_{DDA} = 3.3\text{ V}$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 11](#).

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 12](#).

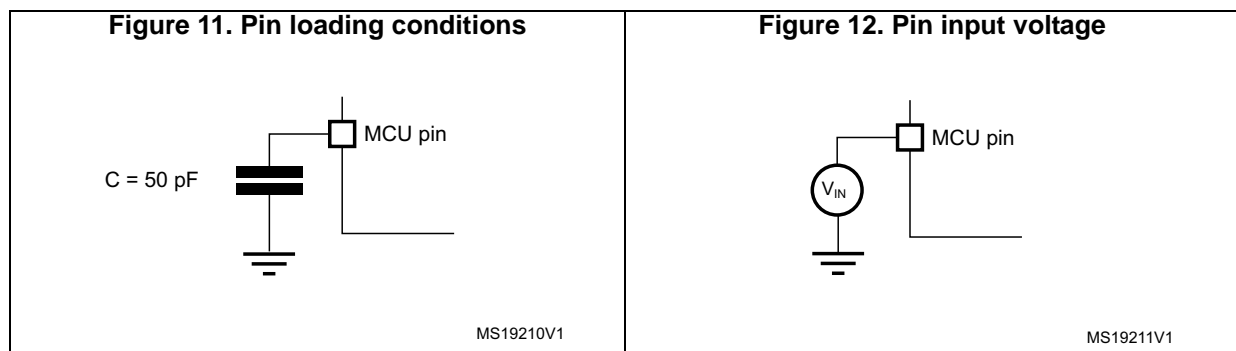


Table 25. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	$\mu\text{s/V}$
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in [Table 26](#) are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 24: General operating conditions](#).

Table 26. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{POR/PDR}^{(1)}$	Power on/power down reset threshold	Falling edge ⁽²⁾	1.80	1.88	1.96 ⁽³⁾	V
		Rising edge	1.84 ⁽³⁾	1.92	2.00	V
$V_{PDRhyst}$	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}^{(4)}$	Reset temporization	-	1.50	2.50	4.50	ms

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD} .
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
3. Data based on characterization results, not tested in production.
4. Guaranteed by design, not tested in production.

Table 27. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	V
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	V
		Falling edge	2.09	2.18	2.27	V
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	V
		Falling edge	2.18	2.28	2.38	V
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	V
		Falling edge	2.28	2.38	2.48	V
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	V
		Falling edge	2.37	2.48	2.59	V
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	V
		Falling edge	2.47	2.58	2.69	V

Table 27. Programmable voltage detector characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Rising edge	2.66	2.78	2.9	V
		Falling edge	2.56	2.68	2.8	V
V_{PVD7}	PVD threshold 7	Rising edge	2.76	2.88	3	V
		Falling edge	2.66	2.78	2.9	V
$V_{PVDhyst}^{(1)}$	PVD hysteresis	-	-	100	-	mV
$I_{DD(PVD)}$	PVD current consumption	-	-	0.15	0.26 ⁽¹⁾	μ A

1. Guaranteed by design, not tested in production.

6.3.4 Embedded reference voltage

The parameters given in [Table 28](#) are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 24: General operating conditions](#).

Table 28. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	$-40\text{ }^{\circ}\text{C} < T_A < +105\text{ }^{\circ}\text{C}$	1.2	1.23	1.25	V
t_{START}	ADC_IN17 buffer startup time	-	-	-	10 ⁽¹⁾	μ s
$t_{S_vrefint}$	ADC sampling time when reading the internal reference voltage	-	4 ⁽¹⁾	-	-	μ s
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	$V_{DDA} = 3\text{ V}$	-	-	10 ⁽¹⁾	mV
T_{Coff}	Temperature coefficient	-	- 100 ⁽¹⁾	-	100 ⁽¹⁾	ppm/ $^{\circ}$ C

1. Guaranteed by design, not tested in production.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 14: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see [Table 35: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 34. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Typ	Unit
I _{sw}	I/O current consumption	V _{DDIOx} = 3.3 V C = C _{INT}	4 MHz	0.07	mA
			8 MHz	0.15	
			16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
		V _{DDIOx} = 3.3 V C _{EXT} = 0 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.18	
			8 MHz	0.37	
			16 MHz	0.76	
			24 MHz	1.39	
			48 MHz	2.188	
		V _{DDIOx} = 3.3 V C _{EXT} = 10 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.32	
			8 MHz	0.64	
			16 MHz	1.25	
			24 MHz	2.23	
			48 MHz	4.442	
		V _{DDIOx} = 3.3 V C _{EXT} = 22 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
		V _{DDIOx} = 3.3 V C _{EXT} = 33 pF C = C _{INT} + C _{EXT} + C _S	4 MHz	0.64	
			8 MHz	1.25	
			16 MHz	3.24	
			24 MHz	5.02	
		V _{DDIOx} = 3.3 V C _{EXT} = 47 pF C = C _{INT} + C _{EXT} + C _S C = C _{int}	4 MHz	0.81	
			8 MHz	1.7	
			16 MHz	3.67	
		V _{DDIOx} = 2.4 V C _{EXT} = 47 pF C = C _{INT} + C _{EXT} + C _S C = C _{int}	4 MHz	0.66	
			8 MHz	1.43	
			16 MHz	2.45	
			24 MHz	4.97	

1. C_S = 7 pF (estimated value).

Table 47. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
N _{END}	Endurance	T _A = -40 to +105 °C	10	kcycle
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	Year
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	
		10 kcycle ⁽²⁾ at T _A = 55 °C	20	

1. Data based on characterization results, not tested in production.

2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 48](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 48. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V _{DD} = 3.3 V, LQFP100, T _A = +25 °C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS} pins to induce a functional disturbance	V _{DD} = 3.3 V, LQFP100, T _A = +25 °C, f _{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value ⁽¹⁾	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforming to ANSI/ESD STM5.3.1	WLCSP64, LQFP100	C3	250	V
			All others	C4	500	

1. Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 51. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in [Table 52](#).

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 61. Comparator characteristics (continued)

Symbol	Parameter	Conditions		Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V_{hys}	Comparator hysteresis	No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	mV
		Low hysteresis (COMPxHYST[1:0]=01)	High speed mode	3	8	13	
			All other power modes	5		10	
		Medium hysteresis (COMPxHYST[1:0]=10)	High speed mode	7	15	26	
			All other power modes	9		19	
		High hysteresis (COMPxHYST[1:0]=11)	High speed mode	18	31	49	
			All other power modes	19		40	

1. Data based on characterization results, not tested in production.

Table 70. UFBGA100 package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 34. Recommended footprint for UFBGA100 package

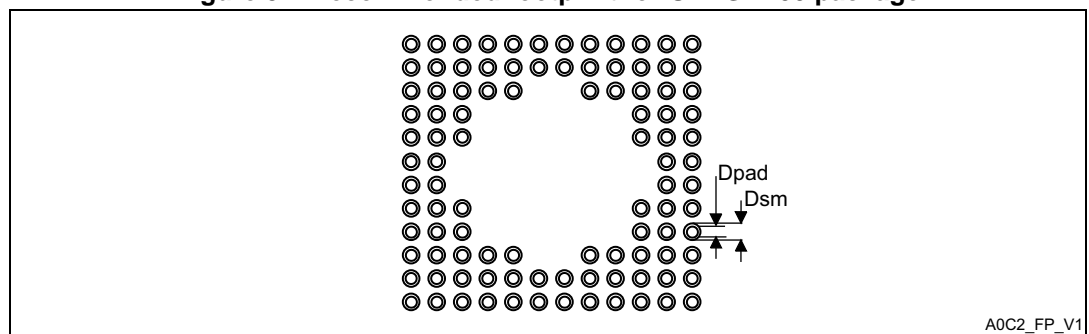


Table 71. UFBGA100 recommended PCB design rules

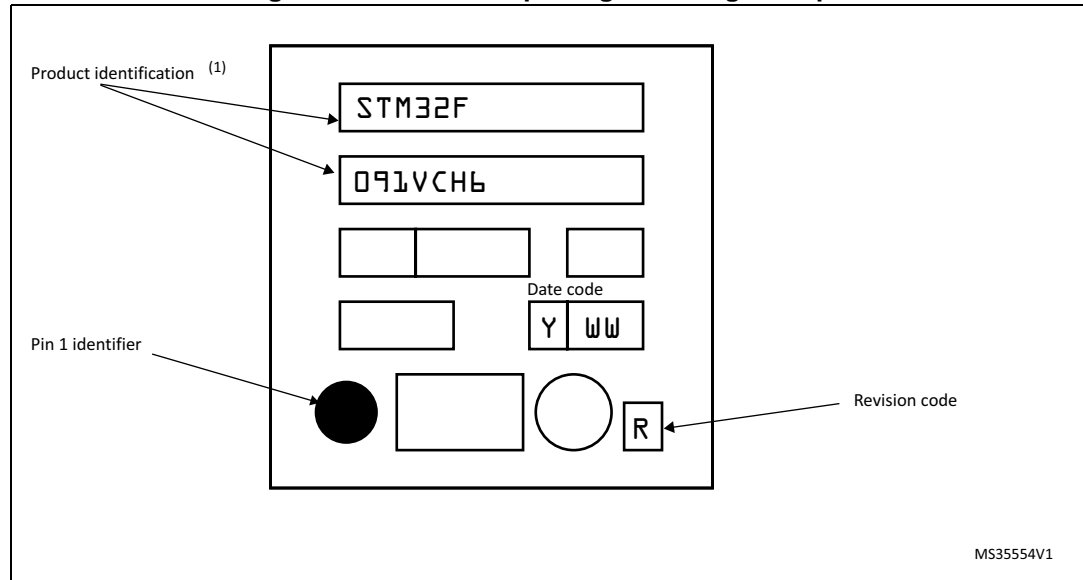
Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 35. UFBGA100 package marking example

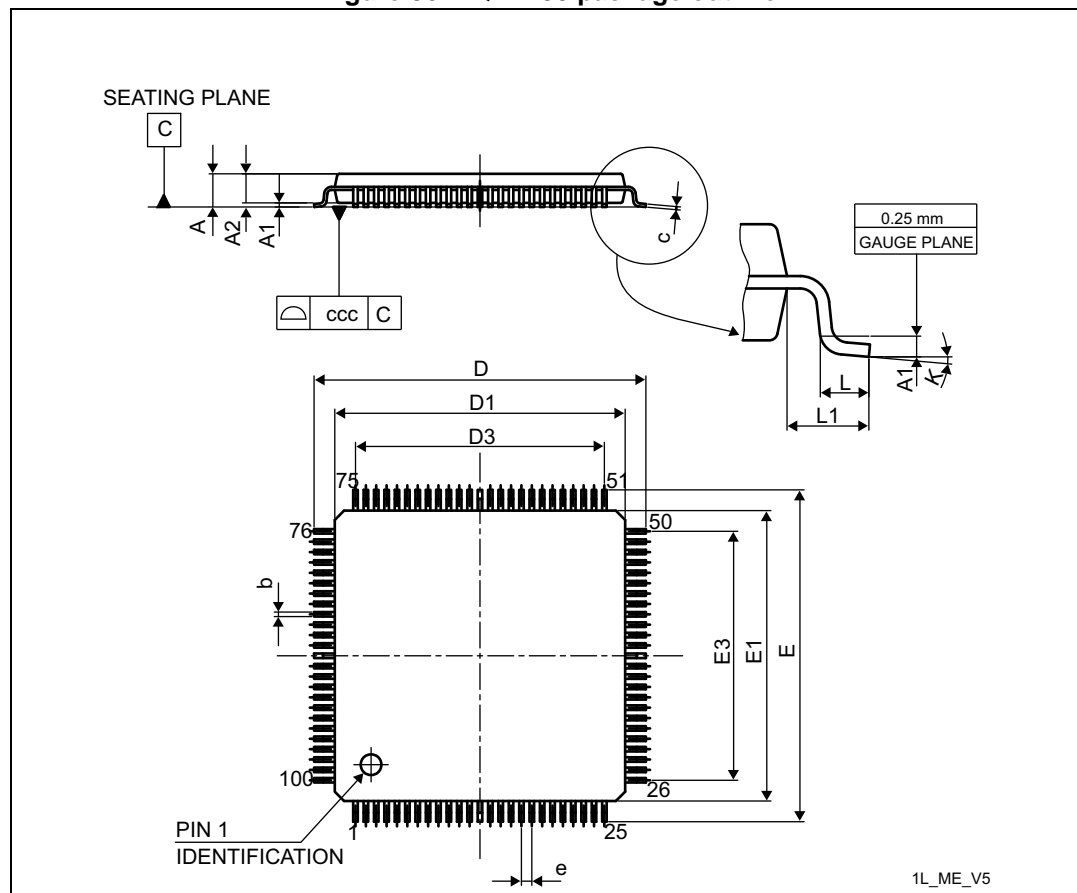


1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

7.2 LQFP100 package information

LQFP100 is a 100-pin, 14 x 14 mm low-profile quad flat package.

Figure 36. LQFP100 package outline



1. Drawing is not to scale.

Table 72. LQFP100 package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378

Table 73. UFBGA64 package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 40. Recommended footprint for UFBGA64 package

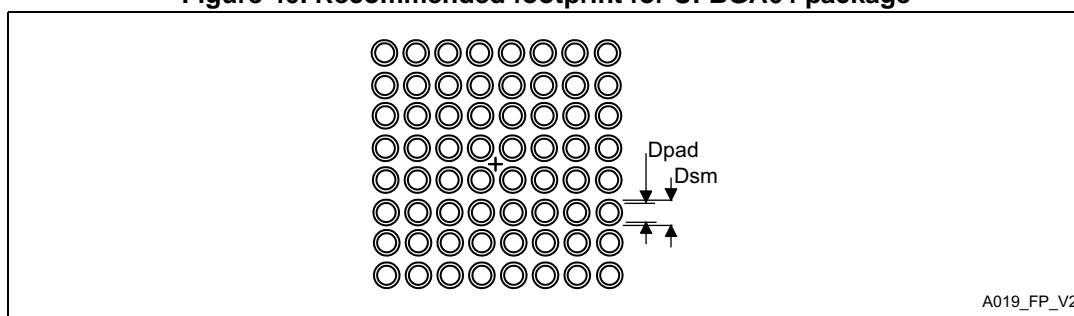


Table 74. UFBGA64 recommended PCB design rules

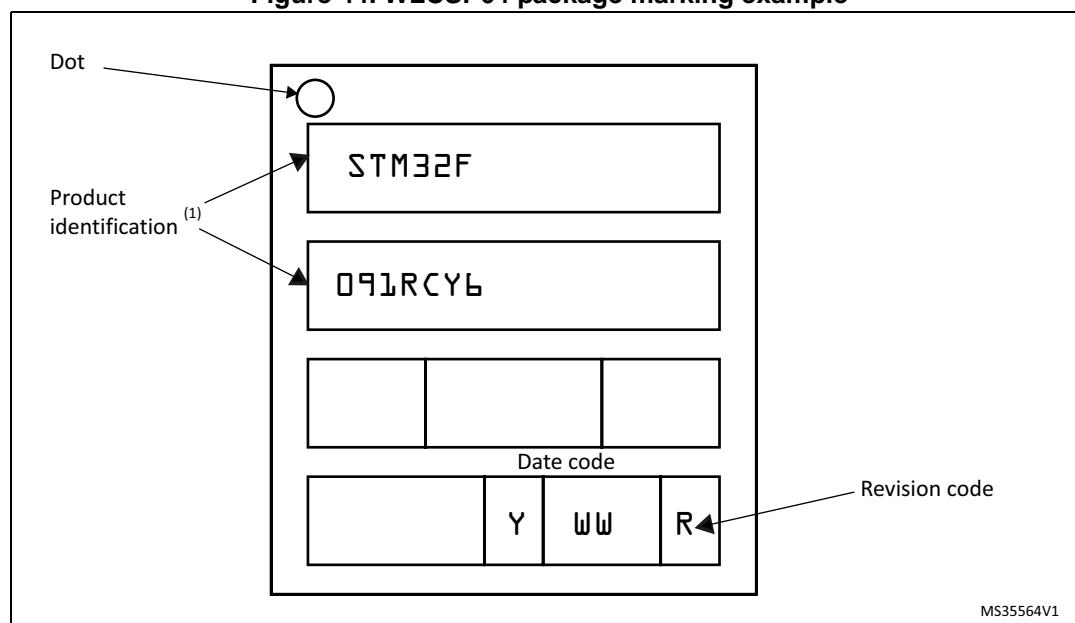
Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 44. WLCSP64 package marking example



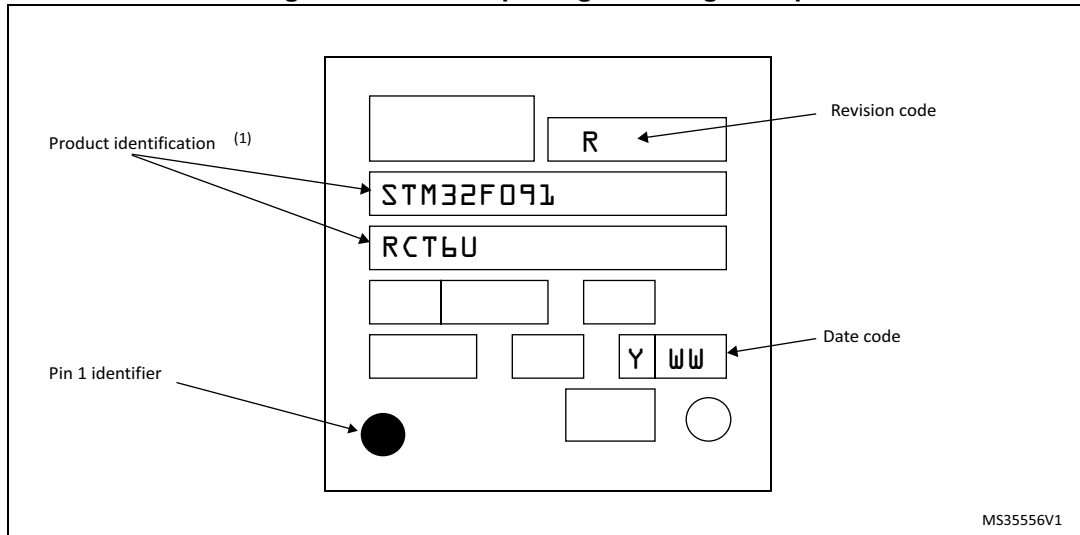
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 47. LQFP64 package marking example



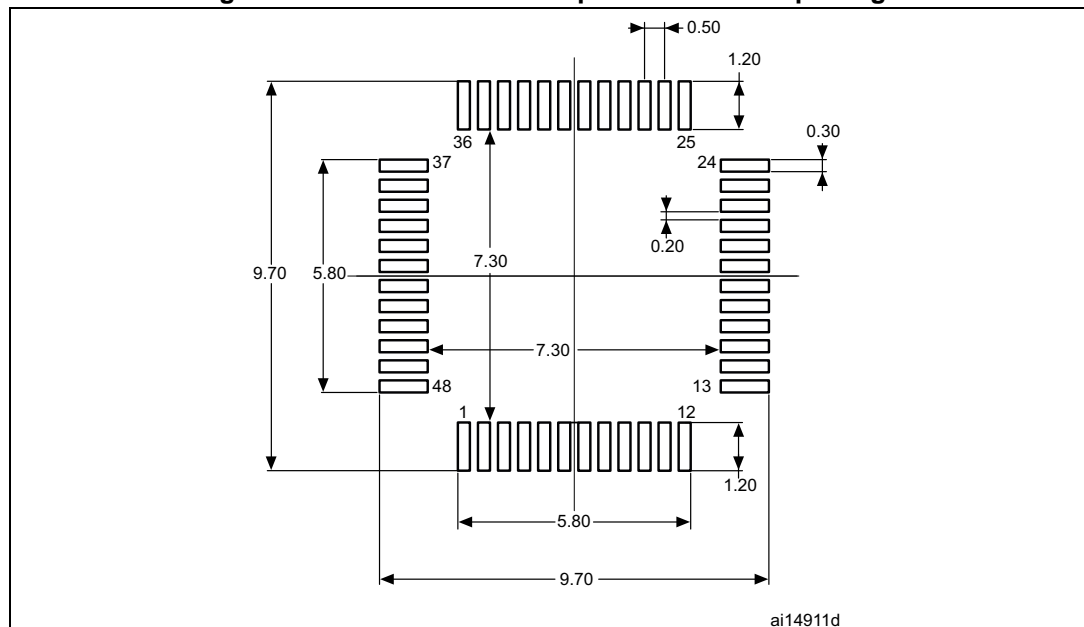
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 78. LQFP48 package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 49. Recommended footprint for LQFP48 package



1. Dimensions are expressed in millimeters.